Schottky barrier diode

RB471E

●**Applications**

Low current rectification
For switching power supplies

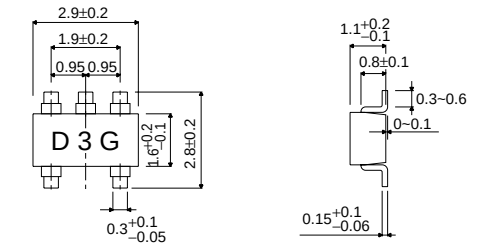
●**Features**

1) Small surface mounting dual element parallel type. (SMD5)
2) Low V_F.(V_F=0.45V Typ. at 100mA)
3) High reliability.

●**Construction**

Silicon epitaxial planar

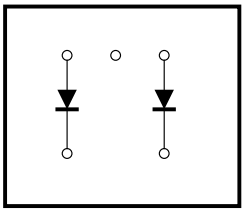
●**External dimensions** (Units : mm)



(All leads have same dimentions)

ROHM : SMD5
EIAJ : SC - 74A
JEDEC : –

●**Circuit**



●**Absolute maximum ratings** (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	40	V
Mean rectifying current	I_O	0.1	A
Peak forward surge current*	I_{FSM}	1	A
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	–40~+125	°C

* 60 Hz for 1 ∿

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{F1}	–	0.28	0.34	V	I_F=10mA
	V_{F2}	–	0.45	0.55	V	I_F=100mA
Reverse current	I_R	–	1	30	μA	V_R=10V
Capacitance between terminals	C_T	–	6.0	–	pF	V_R=10V, f=1MHz

Note) ESD sensitive product handling required.

●Electrical characteristic curves (Ta = 25°C)

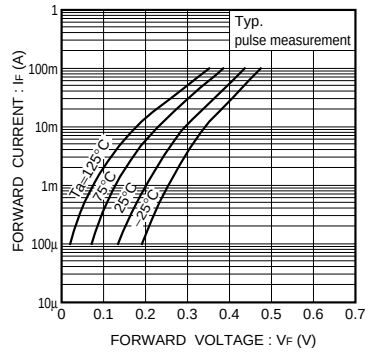


Fig. 1 Forward characteristics

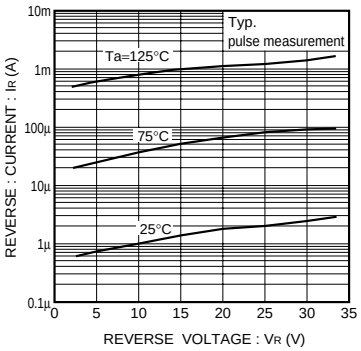


Fig. 2 Reverse characteristics

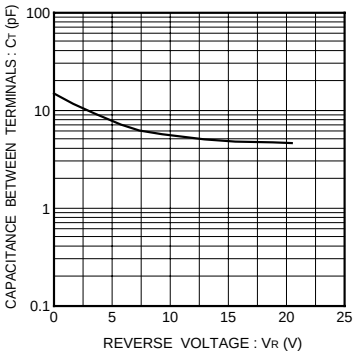


Fig. 3 Capacitance between terminals characteristics

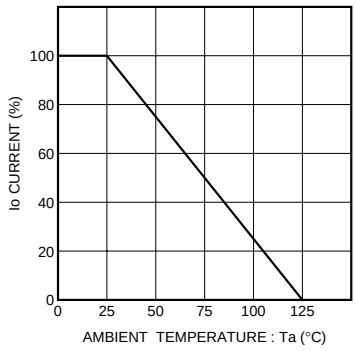


Fig 4. Derating curve
(mounting on glass epoxy PCBs)